

In re application of : Michael A. Todd
App. No. : 10/074,534
Filed : February 11, 2002
For : IMPROVED PROCESS FOR
DEPOSITION OF
SEMICONDUCTOR FILMS
Examiner : Unknown
Art Unit : Unknown

) I hereby certify that this correspondence and all marked
) attachments are being deposited with the United States
) Postal Service as first class mail in an envelope addressed
) to: United States Patent and Trademark Office, P.O. Box
) 2327, Arlington, VA 22202, on

4/9/02
(Date)

Joseph J. Mallon
Joseph J. Mallon, Reg. No. 39,287

UNITED STATES PATENT AND TRADEMARK OFFICE
P.O. Box 2327
Arlington, VA 22202

Sir:

Transmitted herewith is a Preliminary Amendment in the above-identified application.

The fee has been calculated as shown below:

CLAIMS AS FILED					PRESENT EXTRA	RATE	ADDITIONAL FEE	
CLAIMS REMAINING AFTER AMENDMENT	HIGHEST NO. PREVIOUSLY PAID FOR							
Total Claims	33	—	33	=	0	\$18	=	\$0
Independent Claims	3	—	3	=	0	\$84	=	\$0
If application has been amended to contain multiple dependent claim(s), then add						\$130	=	\$0
Time Extension Fee								\$0
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT								\$0

(X) Return prepaid postcard.

(X) Please charge any additional fees, including any fees for additional extension of time, or credit
overpayment to Deposit Account No. 11-1410.

Joseph J. Mallon
Registration No. 39,287
Attorney of Record

ASMEX.367A

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant	:	Michael A. Todd)	Group Art Unit Unknown
)	
Appl. No.	:	10/074,534)	I hereby certify that this correspondence and
)	all marked attachments are being deposited
Filed	:	February 11, 2002)	with the United States Postal Service as first-
)	class mail in an envelope addressed to:
For	:	IMPROVED PROCESS FOR)	United States Patent and Trademark Office,
		DEPOSITION OF)	P.O. Box 2327, Arlington, VA 22202, on
		SEMICONDUCTOR FILMS)	
)	
Examiner	:	Unknown)	

4/9/02
(Date)
Joseph J. Mallon
Joseph J. Mallon, Reg. No. 39,287

PRELIMINARY AMENDMENT

United States Patent and Trademark Office
P.O. Box 2327
Arlington, VA 22202

Dear Sir:

Prior to examination, please amend the above-referenced application as follows:

IN THE ABSTRACT:

Please replace the Abstract of the Disclosure with the following new Abstract:

Chemical vapor deposition processes utilize higher order silanes and germanium precursors as chemical precursors. The processes have high deposition rates yet produce more uniform films, both compositionally and in thickness, than films prepared using conventional chemical precursors. In preferred embodiments, higher order silanes are employed to deposit SiGe-containing films that are useful in the semiconductor industry in various applications such as transistor gate electrodes.